

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	7	(257/183 or 257/184 or 257/185 or 257/186) and transistor and metal near contact and (opening or via or cavity or hole or aperture) and side with (insulating or insulative or dielectric) and (semiconductor or chip or die or IC)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/26 15:20
2	BRS	6	(257/187 or 257/188 or 257/189 or 257/190) and transistor and metal near contact and (opening or via or cavity or hole or aperture) and side with (insulating or insulative or dielectric) and (semiconductor or chip or die or IC)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/26 15:21
3	BRS	24	(257/191 or 257/192 or 257/193 or 257/194) and transistor and metal near contact and (opening or via or cavity or hole or aperture) and side with (insulating or insulative or dielectric) and (semiconductor or chip or die or IC)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/26 15:21
4	BRS	21	(257/195 or 257/196 or 257/197 or 257/198) and transistor and metal near contact and (opening or via or cavity or hole or aperture) and side with (insulating or insulative or dielectric) and (semiconductor or chip or die or IC)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/26 15:22
5	BRS	4	(257/199 or 257/200 or 257/201 or 257/741) and transistor and metal near contact and (opening or via or cavity or hole or aperture) and side with (insulating or insulative or dielectric) and (semiconductor or chip or die or IC)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/26 15:22

	Type	Hits	Search Text	DBs	Time Stamp
6	BRS	5	(257/743 or 257/744 or 257/745) and transistor and metal near contact and (opening or via or cavity or hole or aperture) and side with (insulating or insulative or dielectric) and (semiconductor or chip or die or IC)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/06/26 15:23

	Type	Hits	Search Text	DBs
1	BRS	189449	transistor	USPAT
2	BRS	7144	transistor and metal near contact	USPAT
3	BRS	1924331	transistor and metal near contact and (opening or via or cavity or hole or aperture)	USPAT
4	BRS	6021	transistor and metal near contact and (opening or via or cavity or hole or aperture)	USPAT
5	BRS	4300	transistor and metal near contact and (opening or via or cavity or hole or aperture) and side	USPAT
6	BRS	944	transistor and metal near contact and (opening or via or cavity or hole or aperture) and side with (insulating or insulative or dielectric)	USPAT
7	BRS	901	transistor and metal near contact and (opening or via or cavity or hole or aperture) and side with (insulating or insulative or dielectric) and (semiconductor or chip or die or IC)	USPAT